

Anharmonic decay of vibrational states in amorphous silicon

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Abstract

Anharmonic decay rates are calculated for a realistic atomic model of amorphous silicon. The results show that the vibrational states decay on picosecond timescales and follow the two-mode density of states, similar to crystalline silicon, but somewhat faster. Surprisingly little change occurs for localized states. These results disagree with a recent experiment.

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Scholten et al. [1,2] have found long relaxation times of vibrational states (VS) in amorphous silicon (a-Si) and hydrogenated amorphous silicon (a-H:Si), at liquid He temperatures. Hot charge carriers produced by laser pulses excite VS during their thermal relaxation towards the conduction band edges and the time dependence of the VS populations is measured by anti-Stokes Raman spectroscopy. Their main observations are (a) the populations of high frequency VS live about 10 ns, and (b) the relaxation times increase with frequency. Similar results have been reported for Cr^{3+} doped borate glass using far infra-red radiation for the VS excitation [3]. The situation in crystals is very different: optical phonons decay on picosecond timescales and the lifetimes of phonons typically decrease with frequency, as new decay channels become available.

The model of Orbach et al. [4,5] offers an explanation of this controversy. It assumes that most of the VS are localized (fractons, since the localization is implemented for a glass with fractal structure). The mobility edge occurs at low frequencies (≈ 5 meV) and is equated with the Ioffe-Regel limit (IRL), where the wavevector is no longer a quantum number. The only relevant decay channel for the high frequency fractons is decay to another fracton and a low frequency phonon (hopping). The decay to two phonons is kinematically forbidden, and the probability of a three-fracton interaction is considered to be small. The above two experimental observations can then be rationalized [1,5]. However, experiment provides no indication of fractal structure in homogeneous glasses like a-Si.

As an alternative model, Allen and Feldman used the concept of extended and non-propagating modes [6,7] to explain the thermal conductivity of a-Si at high temperatures. Numerical simulations [7,8] show an onset of localization far beyond the IRL. The majority of modes have frequencies between the IRL and the mobility edge, and are extended but not propagating.

So far only harmonic vibrational properties of disordered structures have been systematically studied, but it is natural, in view of the above experiments, to include anharmonic couplings and investigate perturbatively the decay properties of different VS. The situation in crystalline silicon (c-Si) is well understood both experimentally [9,10] and theoretically

[11,12], so the comparison between the crystalline and amorphous cases provides another motivation for the present calculations.

In this Letter we show that contrary to the experimental results the VS in a realistic model of a-Si decay on picosecond scales and their lifetimes decrease with frequency, as in c-Si. First we calculate the linewidths of the zone-center optical phonons in c-Si, using the Stillinger-Weber (SW) interatomic potential [13]. Next we use the same potential to study the decay rates of VS in a model amorphous system of 216 Si atoms. The decay rates of VS in a hypothetical structure of amorphous Si/Ge with the germanium mass increased by the factor of two are then computed and the results are discussed.

It has been known that the SW potential, which consists of the two- and three-body terms, reproduces reasonably well elastic properties of different phases of silicon [14]. Vibrational spectra have been calculated for both crystalline [14,15] and amorphous silicon [7,14], and give reasonable agreement with experiment, overestimating by 15% the high frequency region. The high temperature value of the thermal expansivity [14] and the values of pressure derivative of elastic constants [16] are underestimated by the SW potential, indicating its relatively small anharmonicity.

The decay rate (inverse lifetime) $2\Gamma(j)$ of the mode j with the frequency $\omega(j)$, at a temperature T , is given by [18]

$$2\Gamma(j) = \frac{\hbar^2\pi}{4\omega(j)} \sum_{k,l} \frac{|V(j,k,l)|^2}{\omega(k)\omega(l)} \left(\frac{1}{2} [1 + n(k) + n(l)] \delta[\omega(j) - \omega(k) - \omega(l)] \right. \\ \left. + [n(k) - n(l)] \delta[\omega(j) + \omega(k) - \omega(l)] \right) \quad (1)$$

Here $V(j,k,l)$ are the coefficients of the cubic terms in the expansion of the interatomic potential in normal mode coordinates, and $n(k)$ are the Bose-Einstein occupation factors $[\exp(\hbar\omega(k)/kT) - 1]^{-1}$. Due to lack of translational invariance, the VS in amorphous systems can be characterized according to their frequency only. For phonons in crystals, j denotes both the band index λ and the wavevector $\mathbf{q}$, and the wavevector conservation up to a reciprocal lattice vector is a selection rule in $V(j,k,l)$. Two different physical processes lead to the above equation: (a) decay of the mode j to all energy conserving combinations of k

and l with the temperature factor $1+n(l)+n(k)$, and (b) decay when the mode j is destroyed together with the mode k (and the mode l is created) has the temperature factor $n(k)-n(l)$. Delta functions ensure energy conservation. Note that at zero temperature only the (a) decay exists and at high temperatures the decay grows proportionally to the temperature.

As a test for the SW potential we have carried out the calculation of the decay rates of the zone-center optical phonons in c-Si. In this case only processes (a) are contributing (frequencies of the $\mathbf{q}=\mathbf{0}$ phonons are the highest in the vibrational spectrum). By identifying the decay rates with the full widths at half maxima of Raman absorption lines, one can also make comparison with experiment. The sum over the $\mathbf{q}$ points in Eq. (1) is performed by the tetrahedron method, using 1772 tetrahedra in the irreducible wedge of the Brillouin zone. Figure 1 shows the temperature dependence of the decay rate along with the experimental values from Ref. [10]. At zero temperature our calculated decay rate is 0.064 meV, as compared to 0.153 meV obtained experimentally [10], and 0.059 meV [11] and 0.183 meV [12] obtained using the local density approximation. In accord with the results of the thermal expansion [14] and pressure dependence of elastic constants [16], we find the SW potential underestimating anharmonic effects. The dominant decay mechanism involves one LA and one TA mode ($\approx 93\%$), while the diagonal LA + LA Klemens channel [19] gives a relatively small contribution ($\approx 7\%$). This follows from the trends in the vibrational density of states, as observed earlier [11,12].

To study the decay rates in a-Si we represent its structure by a cubic unit cell of side 16.35 Å, containing 216 atoms (27 fcc unit cells), and periodic boundary conditions. The random network model atomic coordinates by Wooten, Winer, and Weaire [17], are further relaxed to a local minimum of the SW potential [14]. We use the same potential for the interatomic interactions. Harmonic vibrational properties of the model have been reported elsewhere [7]. Only about 3% of VS above the mobility edge $\omega_c \approx 71$ meV are localized and most of the modes are extended. Only modes with $\omega \lesssim 15$ meV are marginally propagating (partial memory of a wavelength remains). The lowest frequency modes ($\lesssim 10$ meV) are affected by finite size of our sample and are omitted from our calculations.

Due to the discreteness of the vibrational energy levels in our finite system, we represent the delta functions in the Eq. 1 by normalized rectangles of the widths 0.4 meV, centered at the VS frequencies $\omega(j)$. On average there are 3.6 modes in a rectangle. Increase of the rectangle widths increases the computation time without a notable change in results. Smaller values enhance the noise. In Fig.2 we show the calculated decay rates as frequency functions at 10K and 300K. The curves were convolved with rectangles to suppress the remaining noise. The decay rates $2\Gamma(j)$ are of order $0.01 \omega(j)$, which confirms the applicability of lowest order perturbation theory. For lifetimes one thus obtains picoseconds in contrast to the experimentally claimed nanoseconds ($\hbar/1 \text{ meV} \approx 0.7 \text{ ps}$). The decay rate follows the joint two-mode density of states ($\sum_{j,k} \delta[\omega - \omega(j) - \omega(k)]$) curve, even beyond the mobility edge (indicated by the vertical line). Since the localized states in our system kinematically decay mostly to two extended states, the decay properties of the localized states resemble those of the extended states. At higher temperatures the mid-frequency region becomes more pronounced due to the appearance of processes (b). The high temperature shape of the decay rate frequency dependence can be shown to follow a combination of the joint and difference two-mode density of states. Figure 3 provides information about the distribution of the anharmonic matrix elements $V(j,k,l)$, corresponding to the decay of the extended mode j to modes k and l . To improve statistics we combined the information from three (randomly chosen) j modes with frequencies between 65 and 68 meV. Since there are no selection rules present for the decay of the extended modes (other than the energy conservation), all kinematically allowed final states contribute on average equally to the decay. Individual matrix elements occur with a Gaussian distribution reflecting the disorder present in the amorphous structure, and the complete destruction of wavevector selection rules.

We now ask what changes would occur in decay rates if a greater portion of the states were localized. To accomplish this we model a hypothetical alloy of silicon and heavy germanium (a-Si/Ge) by changing the masses of 50% of the atoms chosen at random, to twice the germanium mass. The interatomic potential is unchanged. Harmonic vibrational properties of this systems were studied [7], and it was shown that the mobility edge shifts down to 31

meV. The extrinsic mass disorder increases the portion of localized states. Figure 4 shows the decay rate frequency functions at two temperatures, 10 K and 300 K. The mobility edge is indicated by the vertical line. Again, there are no dramatic changes beyond the mobility edge, the curves basically follow the trends in the joint, and the joint plus the difference two-mode density of states. Modes with frequencies above 62 meV are like the modes of the fracton model, as they decay kinematically only via hopping; allowed decays through three-localized mode interaction are of negligible probability. In order for a localized mode to decay to another localized mode and an extended one, the two localized modes must overlap. As the localization length of the localized modes decreases with frequency, the overlap probability decreases. The deficiency in the number of hopping decay channels is in our model compensated by the increase in magnitude of the hopping matrix elements (squares of the vibrational amplitudes scale inversely with the localization length). We therefore find similar decay rates for the localized and extended states, although their decay mechanisms are very different.

Compared with the decay of the optical phonons in c-Si, the decay rates of the a-Si VS just below the mobility edge are larger by a factor of three. Considering the bond-angle and other structural disorder in a-Si, this seems reasonable. However, the spectral characteristics of the final decay products are very different for the two cases. All kinematically allowed decay channels contribute random terms in the a-Si case (Fig.3), while due to translational invariance there is only a small spectral region of allowed decay products in the c-Si case [11,12]. As in the case of hopping, the deficiency is compensated by the larger magnitudes of the decay matrix elements in c-Si.

In conclusion, we have found that the high-frequency VS in a realistic model of a-Si decay on picosecond time scales, and at low temperatures their lifetimes decrease as frequency increases. This is in contrast to recent experimental claims that the modes decay on nanosecond scales and their lifetimes increase as frequency increases. Two remarks about the experiment are appropriate. First, the average (non-equilibrium) population of the excited VS is $\bar{n}(j) \approx 0.2$ and the VS are excited over the whole spectrum [2]. However, decay

rates $2\Gamma(j)$, Eq. 1, are defined for *small* deviations of *single-frequency* VS populations from equilibrium. It is not clear that the experiment measures the same rates. Second, the VS population is excited through the relaxation of hot carriers. In amorphous systems carriers trapped in localized states in band tails can decay on timescales much larger than picoseconds and replenish the VS population. It is possible that the experiment probes the slow relaxation of the coupled system of trapped carriers and VS, and not the intrinsic VS decay.

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FIG. 1. Decay rate of the zone-center optical phonons in c-Si from the SW potential as a function of absolute temperature. The filled circles are the experimental points from Ref. 10.

FIG. 2. Anharmonic decay rate of VS in a-Si as a frequency function for temperatures 10 K and 300 K. The dashed line in the low temperature graph is the joint two-mode density of states in arbitrary units and the vertical line indicates the mobility edge $\omega_c \approx 71$ meV.

FIG. 3. (a) Distribution of the anharmonic matrix elements $V(j,k,l)$ for the decay of a sample of three extended normal modes j of $\omega(j)$ between 65 and 68 meV. The horizontal frequency axis is the lower frequency of the two final states k and l ; the other frequency is given by the energy conservation $\omega(j) = \omega(k) + \omega(l)$. (b) The number of occurrences of the anharmonic matrix elements from (a) shows their Gaussian random character due to lack of selection rules other than the energy conservation.

FIG. 4. Anharmonic decay rate of VS in hypothetical (see text) a-Si/Ge as a frequency function for temperatures 10 K and 300 K. The vertical line indicates the mobility edge $\omega_c \approx 31$ meV.







